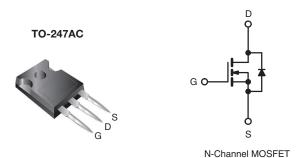


Power MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	600		
$R_{DS(on)}\left(\Omega\right)$	V _{GS} = 10 V 1.2		
Q _g (Max.) (nC)	60		
Q _{gs} (nC)	8.3		
Q _{gd} (nC)	30		
Configuration	Single		



FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- · Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC





DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

TO-247AC The package preferred commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	IRFPC40PbF
Lead (Pb)-life	SiHFPC40-E3
SnPb	IRFPC40
	SiHFPC40

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage			V _{DS}	600	V
Gate-Source Voltage			V_{GS}	± 20	V
Continuous Proin Current	\/ at 10 \/	$T_{\rm C} = 25 ^{\circ}{\rm C}$ $T_{\rm C} = 100 ^{\circ}{\rm C}$		6.8	
Continuous Drain Current V _{GS} at 10 V		T _C = 100 °C	l _D	4.3	Α
Pulsed Drain Current ^a			I _{DM}	27	
Linear Derating Factor				1.2	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	410	mJ
Maximum Power Dissipation $T_C = 25 ^{\circ}C$		P_{D}	150	W	
Peak Diode Recovery dV/dtc			dV/dt	3.0	V/ns
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 150	°C	
Soldering Recommendations (Peak Temperature) for 10 s			300 ^d	7	
M			10	lbf ⋅ in	
Mounting Torque	6-32 or M3 screw			1.1	N · m

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. $V_{DD} = 50$ V, starting $T_J = 25$ °C, L = 16 mH, $R_g = 25$ Ω , $I_{AS} = 6.8$ A (see fig. 12). c. $I_{SD} \le 6.8$ A, $I_{AS} = 6.8$ A (see fig. 12).
- d. 1.6 mm from case

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R _{thJA}	-	40	
Case-to-Sink, Flat, Greased Surface	R _{thCS}	0.24	-	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	-	0.83	

PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						•	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$	V, I _D = 250 μA	600	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Reference t	to 25 °C, I _D = 1 mA	-	0.70	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V$	_{GS} , I _D = 250 μA	2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _G	_S = ± 20 V	-	-	± 100	nA
Zoro Coto Voltogo Duoin Comunit	1	V _{DS} = 6	00 V, V _{GS} = 0 V	-	-	100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 480 V, V	/ _{GS} = 0 V, T _J = 125 °C	-	-	500	μA
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 4.1 A ^b	-	-	1.2	Ω
Forward Transconductance	9 _{fs}	V _{DS} = 10	00 V, I _D = 4.1 A ^b	4.9	-	-	S
Dynamic		·					
Input Capacitance	C _{iss}	V	_{GS} = 0 V,	-	1300	-	
Output Capacitance	C _{oss}	V	$_{0S} = 25 \text{ V},$	-	160	-	pF
Reverse Transfer Capacitance	C _{rss}	f = 1.0	f = 1.0 MHz, see fig. 5		30	-	
Total Gate Charge	Qg		V _{GS} = 10 V	-	-	60	
Gate-Source Charge	Q _{gs}	V _{GS} = 10 V		-	-	8.3	nC
Gate-Drain Charge	Q_{gd}		-	-	30		
Turn-On Delay Time	t _{d(on)}			-	13	-	
Rise Time	t _r	Vpp = 30	00 V, I _D = 6.2 A ,	-	18	-	
Turn-Off Delay Time	t _{d(off)}	$R_g = 9.1 \Omega$, $R_D = 47 \Omega$, see fig. 10^b		-	55	-	ns
Fall Time	t _f			-	20	-	1
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") fro	m is	-	5.0	-	-11
Internal Source Inductance	L _S	package and ce die contact	nter of	-	13	-	- nH
Drain-Source Body Diode Characteristic	s						
Continuous Source-Drain Diode Current	I _S	MOSFET symbo	MOSFET symbol showing the		-	6.8	A
Pulsed Diode Forward Current ^a	I _{SM}	integral reverse p - n junction diode		-	-	27	A .
Body Diode Voltage	V_{SD}	T _J = 25 °C, I _S	_S = 6.8 A, V _{GS} = 0 V ^b	-	-	1.5	V
Body Diode Reverse Recovery Time	t _{rr}	T - 25 °C 1	2 0 A dI/dt = 100 A/v-h	-	450	940	ns
Body Diode Reverse Recovery Charge	Q _{rr}	$T_J = 25 ^{\circ}\text{C}, I_F = 6.2 \text{A}, dI/dt = 100 \text{A/} \mu \text{s}^{\text{b}}$		-	3.8	7.9	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-o		-on is do	minated h	v L and	1.5/

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width \leq 300 μ s; duty cycle \leq 2 %.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

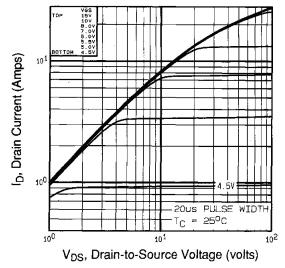


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

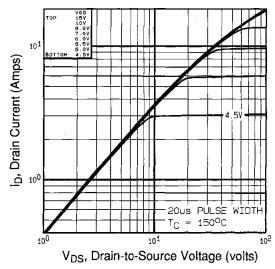


Fig. 2 - Typical Output Characteristics, T_C = 150 °C

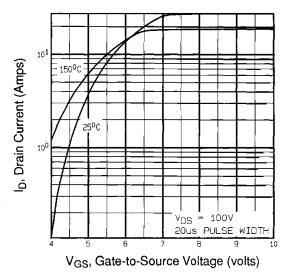


Fig. 3 - Typical Transfer Characteristics

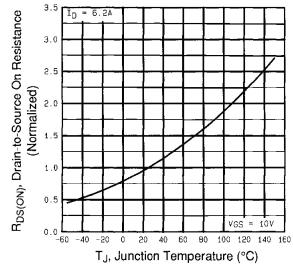


Fig. 4 - Normalized On-Resistance vs. Temperature



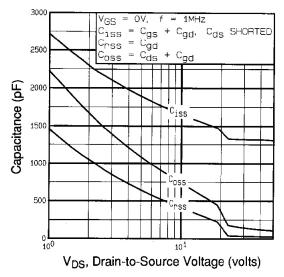


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

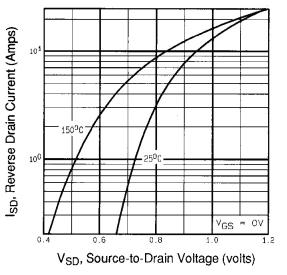


Fig. 7 - Typical Source-Drain Diode Forward Voltage

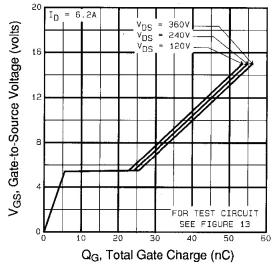


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

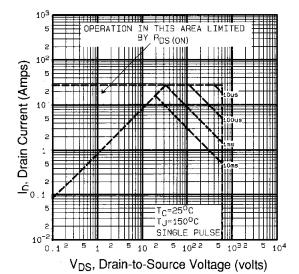


Fig. 8 - Maximum Safe Operating Area





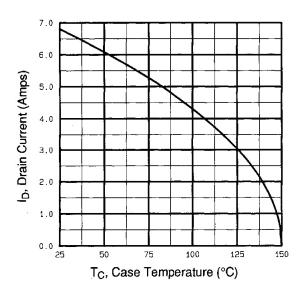


Fig. 9 - Maximum Drain Current vs. Case Temperature

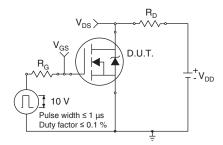


Fig. 10a - Switching Time Test Circuit

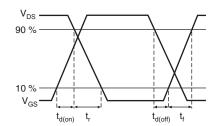


Fig. 10b - Switching Time Waveforms

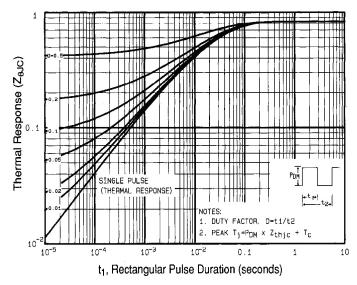


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



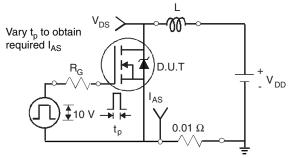


Fig. 12a - Unclamped Inductive Test Circuit

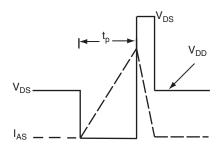


Fig. 12b - Unclamped Inductive Waveforms

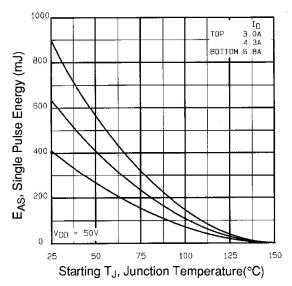


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

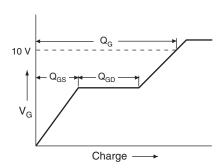


Fig. 13a - Basic Gate Charge Waveform

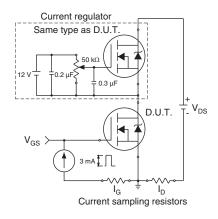
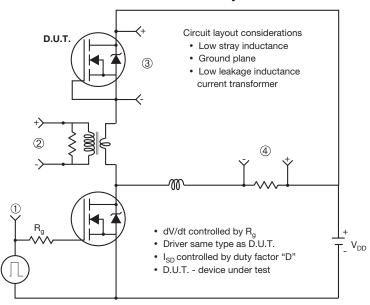


Fig. 13b - Gate Charge Test Circuit



Peak Diode Recovery dV/dt Test Circuit



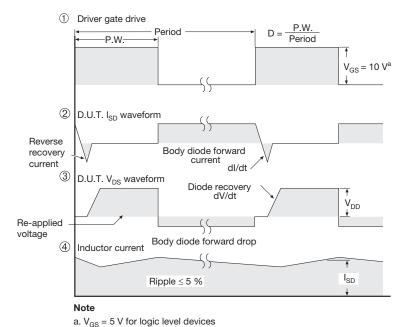


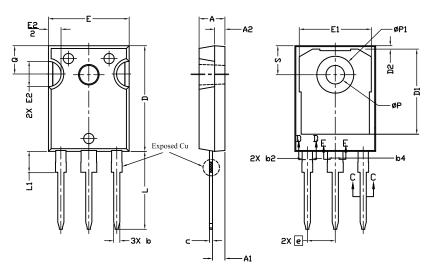
Fig.14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91240.

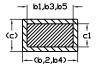


TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D--D,E--E

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

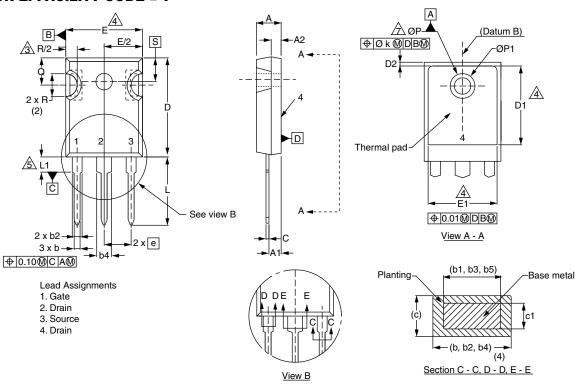
	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	
L		I	1

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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VERSION 2: FACILITY CODE = Y



	MILLIN		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

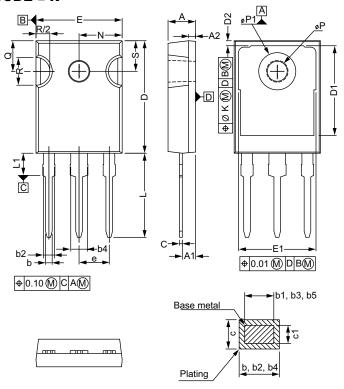
	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46	BSC	
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62 BSC		
Р	3.56	3.66	
P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



Vishay

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